IN THE CLAIMS

Please amend claims 22, 26, 27 and 33. Please add new claims 34 and 35. Please cancel claims 25 and 32. All currently pending claims and status indicators are set forth below:

1-13. (Canceled)

14. (Original) A method of simultaneously accessing a plurality of memory array blocks in a synchronous random access memory (SRAM) device, comprising the acts of:

receiving a first signal at a first input of a logical device, the first signal corresponding to a memory array block selection signal;

receiving a second signal at a second input of the logical device, the second signal corresponding to a testmode enable signal;

producing an output signal from the logical device, wherein the output signal corresponds to one of the first signal and the second signal;

enabling a plurality of memory array block select lines in response to the output signal from the logical device; and

writing data to a plurality of memory array blocks corresponding to the enabled memory array block select lines.

15. (Original) The method of simultaneously accessing a plurality of memory array blocks in a synchronous random access memory (SRAM) device, as set forth in claim 14, wherein the acts of receiving comprise receiving the first signal and the second signal at a NAND gate.

16. (Original) The method of simultaneously accessing a plurality of memory array blocks in a synchronous random access memory (SRAM) device, as set forth in claim 14, comprising:

producing an output signal from the logical device, wherein the output signal corresponds to the testmode enable signal;

enabling a plurality of memory array block select lines in response to the output signal, each of the plurality of memory array block select lines corresponding to one of a plurality of memory array blocks; and

writing data to the plurality of memory array blocks.

17-21. (Canceled)

22. (Currently Amended)   A method of programming/burning-in ~~o~~an SRAM compris~~ing~~es:

selecting a plurality of memory array blocks in the SRAM; and

simultaneously writing to each of the plurality of memory array blocks during burn-in testing, wherein simultaneously writing comprises transmitting data to a plurality of local write drivers.

23. (Previously presented)   The method, as set forth in claim 22, wherein selecting comprises:

providing a block selection signal and a testmode signal to a logical device.

24. (Previously presented)   The method, as set forth in claim 22, wherein selecting comprises:

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providing a clock selection signal and a testmode signal to a NAND gate.

25. (Canceled)

26. (Currently Amended)   The method, as set forth in claim 2522, comprising driving the data from each of the plurality of local write drivers to a respective one of the plurality of memory array blocks.

27. (Currently Amended)   A method of programming/burning-in an SRAM comprising:

        combining a plurality of signals produced externally with respect to the SRAM;

        producing an internal signal configured to simultaneously select a plurality of

            memory array blocks in the SRAM; and

        simultaneously writing to each of the plurality of memory array blocks, wherein

            simultaneously writing comprises transmitting data to a plurality of local

            write drivers.

28. (Previously presented)   The method, as set forth in claim 27, wherein combining comprises combining the plurality of signals through a logical device located internally with respect to the SRAM.

29. (Previously presented)   The method, as set forth in claim 28, wherein producing comprises producing an internal signal from an output of the logical device.

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30. (Previously presented)   The method, as set forth in claim 27, wherein combining comprises combining the plurality of signals through a logical device located internally with respect to the NAND gate.

31. (Previously presented)   The method, as set forth in claim 27, wherein simultaneously writing comprises simultaneously writing to each of the plurality of memory array blocks during burn-in.

32. (Canceled)

33. (Currently Amended)   The method, as set forth in claim 3227, comprising driving the data from each of the plurality of local write drivers to a respective one of the plurality of memory array blocks.

34. (New)   A method of programming/burning-in an SRAM comprising:

    selecting a plurality of memory array blocks in the SRAM, wherein selecting

        comprises providing a block selection signal and a testmode signal to a

        logical device; and

    simultaneously writing to each of the plurality of memory array blocks during

        burn-in testing.

35. (New)   A method of programming/burning-in an SRAM comprising:

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selecting a plurality of memory array blocks in the SRAM, wherein selecting

comprises providing a clock selection signal and a testmode signal to a

NAND gate; and

simultaneously writing to each of the plurality of memory array blocks during

burn-in testing.